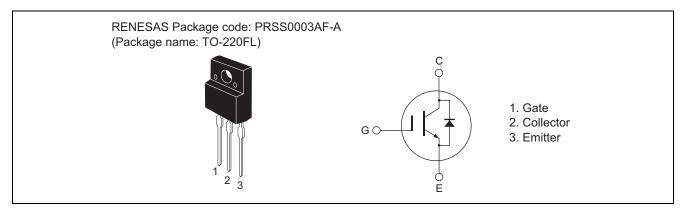


Silicon N Channel IGBT Application: Inverter

## Features

- High breakdown-voltage
- Low on-voltage
- Built-in diode

## Outline



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item Collector to emitter voltage / diode reverse voltage		Symbol	Ratings	Unit	
		V <sub>CES</sub> / V <sub>R</sub>	600	V	
Gate to emitter voltage		V <sub>GES</sub>	±30	V	
Collector current	Tc = 25°C	lc	16	А	
	Tc = 100°C	lc	8	А	
Collector peak current		ic(peak) <sup>Note1</sup>	32	А	
Collector to emitter diode forward current		İ <sub>DF</sub>	8	А	
Collector to emitter diode forward peak current		i <sub>D</sub> (peak) <sup>Note1</sup>	32	А	
Collector dissipation		Pc <sup>Note2</sup>	20	W	
Junction to case thermal impedance		θj-c <sup>Note2</sup>	6.25	°C/ W	
Junction temperature		Tj	150	°C	
Storage temperature		Tstg	-55 to +150	°C	

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tc = 25°C

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## **Electrical Characteristics**

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						(Ta = 25°C)	
ltem	Symbol	Min	Тур	Max	Unit	Test Conditions	
Zero gate voltage collector current / Diode reverse current	I <sub>CES</sub> / I <sub>R</sub>	—	—	100	μΑ	V <sub>CE</sub> = 600 V, V <sub>GE</sub> = 0	
Gate to emitter leak current	I <sub>GES</sub>	_	_	±1	μA	$V_{GE} = \pm 30 \text{ V}, \text{ V}_{CE} = 0$	
Gate to emitter cutoff voltage	V <sub>GE(off)</sub>	4.0	_	6.0	V	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 1 mA	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	_	1.8	2.2	V	$I_{C}$ = 8 A, $V_{GE}$ = 15 V <sup>Note3</sup>	
	V <sub>CE(sat)</sub>	_	2.3	_	V	I <sub>C</sub> =16 A, V <sub>GE</sub> = 15 V <sup>Note3</sup>	
Input capacitance	Cies	_	290	_	pF	V <sub>CE</sub> = 25 V	
Output capacitance	Coes	_	25	_	pF	V <sub>GE</sub> = 0	
Reveres transfer capacitance	Cres	_	7.5	_	pF	f = 1 MHz	
Total gate charge	Qg	—	12.0	_	nC	V <sub>GE</sub> = 15 V	
Gate to emitter charge	Qge	_	2.0		nC	V <sub>CE</sub> = 300 V	
Gate to collector charge	Qgc	_	6.0	_	nC	I <sub>C</sub> = 8 A	
Switching time	t <sub>d(on)</sub>	_	25		ns	I <sub>C</sub> = 8 A	
	tr	_	35		ns	R <sub>L</sub> = 37.5 Ω	
	t <sub>d(off)</sub>	_	40		ns	V <sub>GE</sub> = 15 V	
	t <sub>f</sub>	—	100		ns	Rg = 5 Ω	

FRD Forward voltage	VF		1.8	2.3	V	I <sub>F</sub> = 8 A <sup>Note3</sup>
FRD reverse recovery time	trr	—	100	—	ns	I <sub>F</sub> = 8 A
						di⊧/dt = 100 A/µs

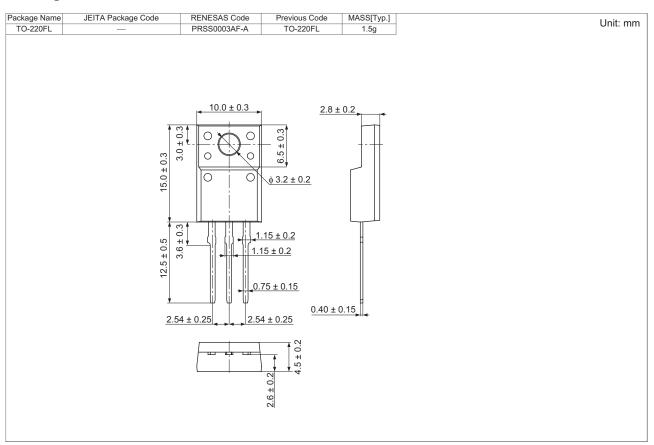
Notes: 3. Pulse test.

4. Under development -The specifications potentially be changed without notice.

## Preliminary

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## **Package Dimension**



## **Ordering Information**

Part No. Quantity		Shipping Container		
RJH60D1DPP-M0-T2	1050 pcs	Box (Tube)		

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